# **100 mA Negative Voltage Regulators**

The MC79L00A Series negative voltage regulators are inexpensive, easy-to-use devices suitable for numerous applications requiring up to 100 mA. Like the higher powered MC7900 Series negative regulators, this series features thermal shutdown and current limiting, making them remarkably rugged. In most applications, no external components are required for operation.

The MC79L00A devices are useful for on-card regulation or any other application where a regulated negative voltage at a modest current level is needed. These regulators offer substantial advantage over the common resistor/Zener diode approach.

#### Features

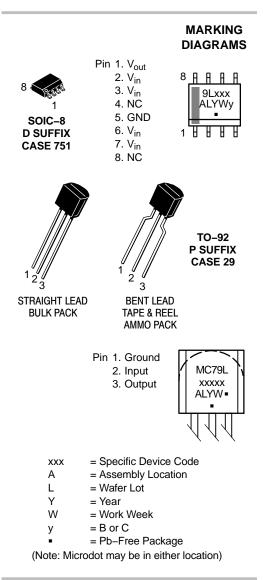
- No External Components Required
- Internal Short Circuit Current Limiting
- Internal Thermal Overload Protection
- Low Cost
- Complementary Positive Regulators Offered (MC78L00 Series)
- Pb-Free Packages are Available



## **ON Semiconductor®**

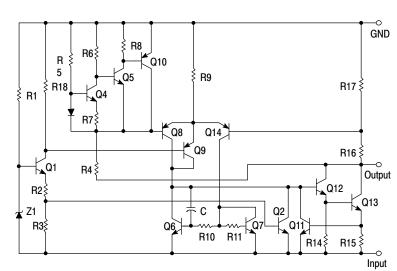
www.onsemi.com

# THREE-TERMINAL LOW CURRENT NEGATIVE FIXED VOLTAGE REGULATORS



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.



\* Automotive temperature range selections are available with special test conditions and additional tests in 5, 12 and 15 V devices. Contact your local ON Semiconductor sales office for information.

#### Figure 1. Representative Schematic Diagram

#### **MAXIMUM RATINGS** ( $T_A = +25^{\circ}C$ , unless otherwise noted.)

Rating	Symbol	Value	Unit
Input Voltage (-5 V) (-12, -15, -18 V) (-24 V)	VI	-30 -35 -40	Vdc
Power Dissipation Case 29 (TO-92 Type) $T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case Case 751 (SOIC-8 Type) (Note 1) $T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	PD R <sub>θJA</sub> R <sub>θJC</sub> PD R <sub>θJA</sub> R <sub>θJC</sub>	Internally Limited 160 83 Internally Limited 180 45	₩ °C/₩ °C/₩ °C/₩ °C/₩
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Junction Temperature	TJ	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. SOIC-8 Junction-to-Ambient Thermal Resistance is for minimum recommended pad size. Refer to Figure 9 for Thermal Resistance variation versus pad size.

\*This device series contains ESD protection and exceeds the following tests: Human Body Model 2000 V per MIL\_STD\_883, Method 3015 Machine Model Method 200 V.

# **ELECTRICAL CHARACTERISTICS** (V<sub>I</sub> = -10 V, I<sub>O</sub> = 40 mA, C<sub>I</sub> = 0.33 $\mu$ F, C<sub>O</sub> = 0.1 $\mu$ F, -40°C < T<sub>J</sub> +125°C (for MC79LXXAB), 0°C < T<sub>J</sub> < +125°C (for MC79LXXAC)).

		м			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ( $T_J = +25^{\circ}C$ )	V <sub>O</sub>	-4.8	-5.0	-5.2	Vdc
$ \begin{array}{l} \mbox{Input Regulation} (T_J = +25^\circ C) \\ -7.0 \mbox{ Vdc} \geq V_l \geq -20 \mbox{ Vdc} \\ -8.0 \mbox{ Vdc} \geq V_l \geq -20 \mbox{ Vdc} \end{array} $	Reg <sub>line</sub>			150 100	mV
Load Regulation $T_J = +25^{\circ}C$ , 1.0 mA $\le I_O \le 100$ mA 1.0 mA $\le I_O \le 40$ mA	Reg <sub>load</sub>			60 30	mV
Output Voltage -7.0 Vdc $\geq$ V <sub>I</sub> $\geq$ -20 Vdc, 1.0 mA $\leq$ I <sub>O</sub> $\leq$ 40 mA V <sub>I</sub> = -10 Vdc, 1.0 mA $\leq$ I <sub>O</sub> $\leq$ 70 mA	Vo	-4.75 -4.75		-5.25 -5.25	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I <sub>IB</sub>			6.0 5.5	mA
Input Bias Current Change $-8.0 \text{ Vdc} \ge V_I \ge -20 \text{ Vdc}$ $1.0 \text{ mA} \le I_O \le 40 \text{ mA}$	I <sub>IB</sub>	- -	- -	1.5 0.1	mA
Output Noise Voltage (T <sub>A</sub> = +25°C, 10 Hz $\leq$ f $\leq$ 100 kHz)	V <sub>n</sub>	-	40	-	μV
Ripple Rejection (-8.0 $\ge$ V <sub>I</sub> $\ge$ -18 Vdc, f = 120 Hz, T <sub>J</sub> = +25°C)	RR	41	49	-	dB
Dropout Voltage (I <sub>O</sub> = 40 mA, $T_J$ = +25°C)	V <sub>I</sub> –V <sub>O</sub>	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

**ELECTRICAL CHARACTERISTICS** (V<sub>I</sub> = -19 V, I<sub>O</sub> = 40 mA, C<sub>I</sub> = 0.33  $\mu$ F, C<sub>O</sub> = 0.1  $\mu$ F, -40°C < T<sub>J</sub> +125°C (for MC79LXXAB), 0°C < T<sub>J</sub> < +125°C (for MC79LXXAC)).

		Μ			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ( $T_J = +25^{\circ}C$ )	Vo	-11.5	-12	-12.5	Vdc
$ \begin{array}{l} \mbox{Input Regulation } (T_J = +25^\circ C) \\ -14.5 \mbox{ Vdc} \geq V_I \geq -27 \mbox{ Vdc} \\ -16 \mbox{ Vdc} \geq V_I \geq -27 \mbox{ Vdc} \end{array} $	Reg <sub>line</sub>	-		250 200	mV
Load Regulation $T_J = +25^{\circ}C$ , 1.0 mA $\leq I_O \leq$ 100 mA 1.0 mA $\leq I_O \leq$ 40 mA	Reg <sub>load</sub>	-		100 50	mV
$\begin{array}{l} \text{Output Voltage} \\ -14.5 \ \text{Vdc} \geq \text{V}_l \geq -27 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq \text{I}_O \leq 40 \ \text{mA} \\ \text{V}_l = -19 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq \text{I}_O \leq 70 \ \text{mA} \end{array}$	V <sub>O</sub>	-11.4 -11.4		-12.6 -12.6	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I <sub>IB</sub>			6.5 6.0	mA
Input Bias Current Change $-16 \text{ Vdc} \ge V_1 \ge -27 \text{ Vdc}$ $1.0 \text{ mA} \le I_0 \le 40 \text{ mA}$	I <sub>IB</sub>			1.5 0.2	mA
Output Noise Voltage (T <sub>A</sub> = +25°C, 10 Hz $\leq$ f $\leq$ 100 kHz)	V <sub>n</sub>	_	80	-	μV
Ripple Rejection (–15 $\leq$ V <sub>I</sub> $\leq$ –25 Vdc, f = 120 Hz, T <sub>J</sub> = +25°C)	RR	37	42	-	dB
Dropout Voltage ( $I_O = 40 \text{ mA}, T_J = +25^{\circ}C$ )	V <sub>I</sub> –V <sub>O</sub>	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

**ELECTRICAL CHARACTERISTICS** (V<sub>I</sub> = -23 V, I<sub>O</sub> = 40 mA, C<sub>I</sub> = 0.33  $\mu$ F, C<sub>O</sub> = 0.1  $\mu$ F, -40°C < T<sub>J</sub> +125°C (for MC79LXXAB), 0°C < T<sub>J</sub> + 125°C (for MC79LXXAC)).

		M	AB		
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ( $T_J = +25^{\circ}C$ )	V <sub>O</sub>	-14.4	-15	-15.6	Vdc
Input Regulation (T <sub>J</sub> = +25°C) -17.5 Vdc $\ge$ V <sub>I</sub> $\ge$ -30 Vdc -20 Vdc $\ge$ V <sub>I</sub> $\ge$ -30 Vdc	Reg <sub>line</sub>			300 250	mV
Load Regulation $T_J$ = +25°C, 1.0 mA $\leq I_O \leq$ 100 mA 1.0 mA $\leq I_O \leq$ 40 mA	Reg <sub>load</sub>		- -	150 75	mV
Output Voltage -17.5 Vdc $\ge$ V <sub>1</sub> $\ge$ -Vdc, 1.0 mA $\le$ I <sub>O</sub> $\le$ 40 mA V <sub>1</sub> = -23 Vdc, 1.0 mA $\le$ I <sub>O</sub> $\le$ 70 mA	Vo	-14.25 -14.25		-15.75 -15.75	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I <sub>IB</sub>			6.5 6.0	mA
Input Bias Current Change -20 Vdc $\ge$ V <sub>I</sub> $\ge$ -30 Vdc 1.0 mA $\le$ I <sub>O</sub> $\le$ 40 mA	Δl <sub>IB</sub>			1.5 0.1	mA
Output Noise Voltage (T <sub>A</sub> = +25°C, 10 Hz $\leq$ f $\leq$ 100 kHz)	V <sub>N</sub>	-	90	-	μV
Ripple Rejection (-18.5 $\leq$ V <sub>I</sub> $\leq$ -28.5 Vdc, f = 120 Hz)		34	39	-	dB
Dropout Voltage I <sub>O</sub> = 40 mA, $T_J$ = +25°C	V <sub>I</sub> -V <sub>O</sub>	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<b>ELECTRICAL CHARACTERISTICS</b> (V <sub>I</sub> = $-27$ V, I <sub>O</sub> = 40 mA, C <sub>I</sub> = $0.33 \mu$ F, C <sub>O</sub> = $0.1 \mu$ F, $-40^{\circ}$ C < T <sub>J</sub> +125°C (for MC79LXXAB),
$0^{\circ}C < T_{J} < +125^{\circ}C$ (for MC79LXXAC), unless otherwise noted).

			;		
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage (T <sub>J</sub> = +25°C)	Vo	-17.3	–18	-18.7	Vdc
$\begin{array}{l} \mbox{Input Regulation } (T_J = +25^\circ C) \\ -20.7 \ \mbox{Vdc} \geq V_I \geq -33 \ \mbox{Vdc} \\ -21.4 \ \mbox{Vdc} \geq V_I \geq -33 \ \mbox{Vdc} \\ -22 \ \mbox{Vdc} \geq V_I \geq -33 \ \mbox{Vdc} \\ -21 \ \mbox{Vdc} \geq V_I \geq -33 \ \mbox{Vdc} \\ \end{array}$	Reg <sub>line</sub>	- - - -	- - - -	325 _ _ 275	mV
Load Regulation $T_J = +25^{\circ}C$ , 1.0 mA $\le I_O \le 100$ mA 1.0 mA $\le I_O \le 40$ mA	Reg <sub>load</sub>	- -		170 85	mV
$\begin{array}{l} \text{Output Voltage} \\ -20.7 \ \text{Vdc} \geq V_l \geq -33 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq I_O \leq 40 \ \text{mA} \\ -21.4 \ \text{Vdc} \geq V_l \geq -33 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq I_O \leq 40 \ \text{mA} \\ V_l = -27 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq I_O \leq 70 \ \text{mA} \end{array}$	Vo	-17.1 - -17.1	- - -	-18.9 - -18.9	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I <sub>IB</sub>	- -		6.5 6.0	mA
$ \begin{array}{l} \mbox{Input Bias Current Change} \\ -21 \mbox{ Vdc} \geq V_l \geq -33 \mbox{ Vdc} \\ -27 \mbox{ Vdc} \geq V_l \geq -33 \mbox{ Vdc} \\ 1.0 \mbox{ mA} \leq I_O \leq 40 \mbox{ mA} \end{array} $	I <sub>IB</sub>	- - -	- - -	1.5 	mA
Output Noise Voltage (T <sub>A</sub> = +25°C, 10 Hz $\leq$ f $\leq$ 100 kHz)	Vn	_	150	-	μV
Ripple Rejection (–23 $\le$ V <sub>I</sub> $\le$ –33 Vdc, f = 120 Hz, T <sub>J</sub> = +25°C)	RR	33	48	-	dB
Dropout Voltage I <sub>O</sub> = 40 mA, T <sub>J</sub> = +25°C	IVI-VOI	_	1.7	_	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **ELECTRICAL CHARACTERISTICS** (V<sub>I</sub> = -33 V, I<sub>O</sub> = 40 mA, C<sub>I</sub> = 0.33 $\mu$ F, C<sub>O</sub> = 0.1 $\mu$ F, -40°C < T<sub>J</sub> +125°C (for MC79LXXAB), 0°C < T<sub>J</sub> < +125°C (for MC79LXXAC), unless otherwise noted).

Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ( $T_J = +25^{\circ}C$ )	Vo	-23	-24	-25	Vdc
$\begin{array}{l} \mbox{Input Regulation } (T_J=+25^\circ C) \\ -27 \ \mbox{Vdc} \geq V_l \geq -38 \ \mbox{Vdc} \\ -27.5 \ \mbox{Vdc} \geq V_l \geq -38 \ \mbox{Vdc} \\ -28 \ \mbox{Vdc} \geq V_l \geq -38 \ \mbox{Vdc} \end{array}$	Reg <sub>line</sub>			350 	mV
Load Regulation $T_J = +25^{\circ}C$ , 1.0 mA $\leq I_O \leq$ 100 mA 1.0 mA $\leq I_O \leq$ 40 mA	Reg <sub>load</sub>			200 100	mV
$\begin{array}{l} \mbox{Output Voltage} \\ -27 \mbox{ Vdc} \geq V_l \geq -38 \mbox{ V}, \ 1.0 \mbox{ mA} \leq I_O \leq 40 \mbox{ mA} \\ -28 \mbox{ Vdc} \geq V_l \geq -38 \mbox{ Vdc}, \ 1.0 \mbox{ mA} \leq I_O \leq 40 \mbox{ mA} \\ \mbox{ V}_l = -33 \mbox{ Vdc}, \ 1.0 \mbox{ mA} \leq I_O \leq 70 \mbox{ mA} \end{array}$	Vo	-22.8 - -22.8		-25.2 - 25.2	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I <sub>IB</sub>	-		6.5 6.0	mA
Input Bias Current Change -28 Vdc $\ge$ V <sub>1</sub> $\ge$ -38 Vdc 1.0 mA $\le$ I <sub>0</sub> $\le$ 40 mA	Δl <sub>IB</sub>		_ _	1.5 0.1	mA
Output Noise Voltage (T <sub>A</sub> = +25°C, 10 Hz $\leq$ f $\leq$ 100 kHz)	V <sub>n</sub>	-	200	-	μV
Ripple Rejection (-29 $\leq$ V <sub>I</sub> $\leq$ -35 Vdc, f = 120 Hz, T <sub>J</sub> = +25°C)	RR	31	47	-	dB
Dropout Voltage $I_0 = 40 \text{ mA}, T_J = +25^{\circ}\text{C}$	V <sub>I</sub> –V <sub>O</sub>	_	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **APPLICATIONS INFORMATION**

#### **Design Considerations**

The MC79L00A Series of fixed voltage regulators are designed with Thermal Overload Protections that shuts down the circuit when subjected to an excessive power overload condition, Internal Short Circuit Protection that limits the maximum current the circuit will pass.

In many low current applications, compensation capacitors are not required. However, it is recommended that the regulator input be bypassed with a capacitor if the regulator is connected to the power supply filter with long wire length, or if the output load capacitance is large. An input bypass capacitor should be selected to provide good

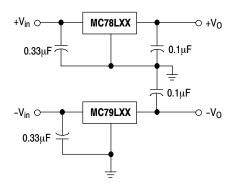
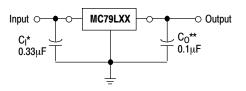


Figure 2. Positive and Negative Regulator

high–frequency characteristics to insure stable operation under all load conditions. A 0.33  $\mu$ F or larger tantalum, mylar, or other capacitor having low internal impedance at high frequencies should be chosen. The bypass capacitor should be mounted with the shortest possible leads directly across the regulator's input terminals. Normally good construction techniques should be used to minimize ground loops and lead resistance drops since the regulator has no external sense lead. Bypassing the output is also recommended.



A common ground is required between the input and the output voltages. The input voltage must remain typically 2.0 V above the output voltage even during the low point on the ripple voltage.

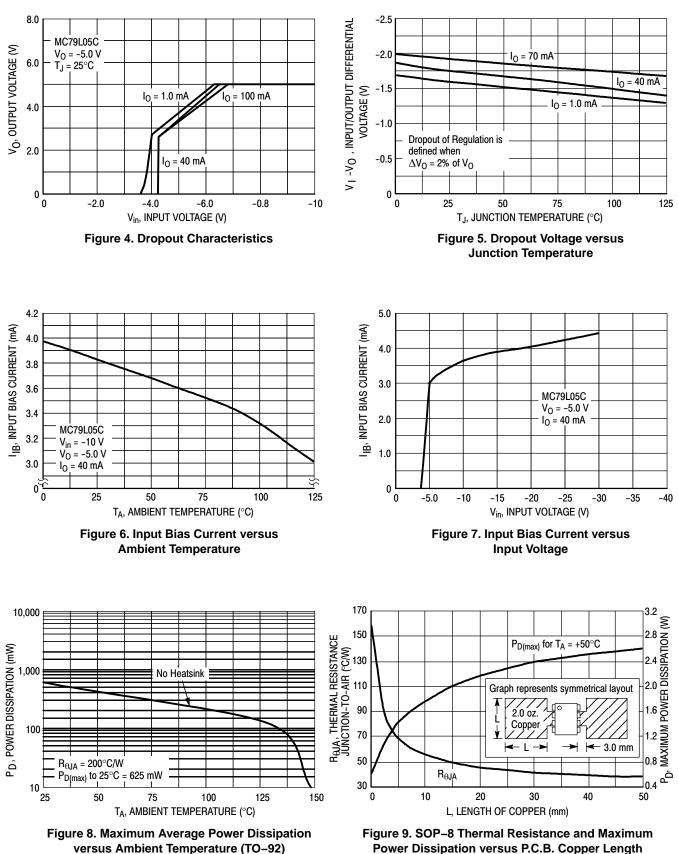
\* C<sub>I</sub> is required if regulator is located an appreciable distance from the power supply filter

\*\* C<sub>O</sub> improves stability and transient response.

**Figure 3. Standard Application** 

### **TYPICAL CHARACTERISTICS**

(T<sub>A</sub> = +25°C, unless otherwise noted.)



#### **ORDERING INFORMATION**

Device	Nominal Voltage	Operating Temperature Range	Package	Shipping <sup>†</sup>
MC79L05ABDG	–5.0 V	$TJ = -40^{\circ}$ to $+125^{\circ}C$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ABPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L05ABPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L05ACDG		TJ = 0° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ACPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L05ACPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L05ACPRMG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L05ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L12ABDG	–12 V	$TJ = -40^{\circ}$ to $+125^{\circ}C$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ABPG			TO–92 (Pb–Free)	2000 Units / Bag
MC79L12ABPRAG			TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L12ACDG	–12 V	$TJ = 0^{\circ} to +125^{\circ}C$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ACPG			TO–92 (Pb–Free)	2000 Units / Bag
MC79L12ACPRAG			TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L12ACPRPG			TO–92 (Pb–Free)	2000 / Tape & Ammo Box

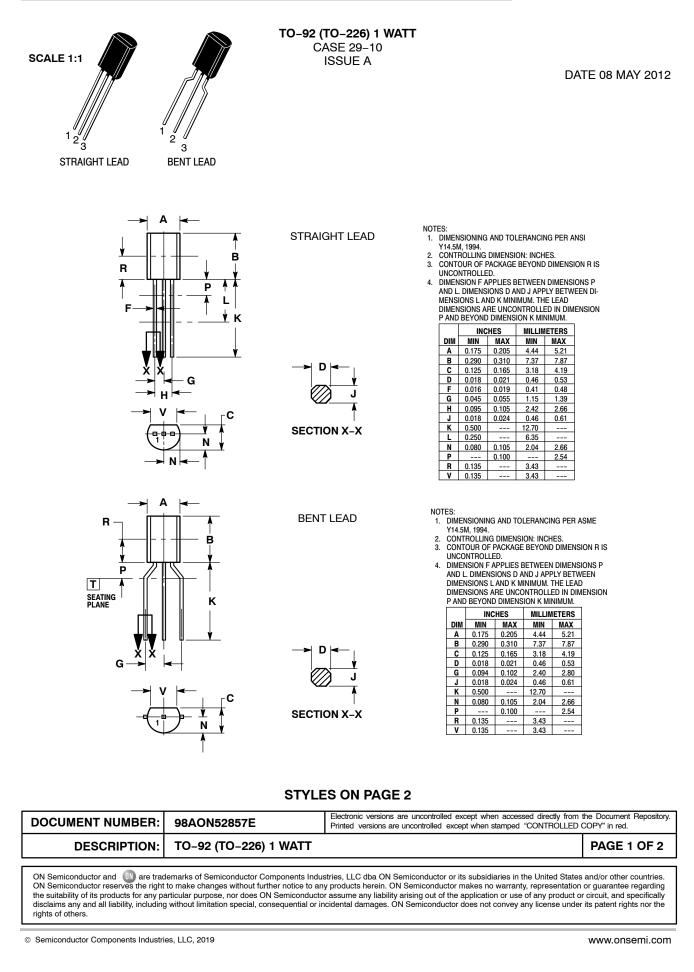
### **ORDERING INFORMATION** (continued)

Device	Nominal Voltage	Operating Temperature Range	Package	Shipping <sup>†</sup>
MC79L15ABDG	–15 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ABDR2G		-	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ABPG		-	TO–92 (Pb–Free)	2000 Units / Bag
MC79L15ABPRPG		-	TO–92 (Pb–Free)	2000 / Tape & Ammo Box
MC79L15ACDG		$TJ = 0^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ACPG			TO–92 (Pb–Free)	2000 Units / Bag
MC79L15ACPRAG		-	TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L15ACPREG		-	TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L15ACPRPG		-	TO–92 (Pb–Free)	2000 / Tape & Ammo Box
MC79L18ABPRPG	–18 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	TO–92 (Pb–Free)	2000 / Tape & Ammo Box
MC79L18ACPG		$TJ = 0^{\circ} \text{ to } +125^{\circ}\text{C}$	TO–92 (Pb–Free)	2000 Units / Bag
MC79L24ABPG	–24 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	TO–92 (Pb–Free)	2000 Units / Bag
MC79L24ACPG		$TJ = 0^{\circ} \text{ to } +125^{\circ}\text{C}$	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ACPRMG		-	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L24ACPRPG			TO–92 (Pb–Free)	2000 / Tape & Ammo Box

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





#### **TO-92 (TO-226) 1 WATT** CASE 29-10 ISSUE A

### DATE 08 MAY 2012

	EMITTER BASE COLLECTOR								
	GATE SOURCE & SUBSTRATE DRAIN								
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 Gate Main Terminal 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
STYLE 21: PIN 1. 2. 3.	COLLECTOR EMITTER BASE	STYLE 22: PIN 1. 2. 3.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER Collector/Anode Cathode	STYLE 25: PIN 1. 2. 3.	MT 1 GATE MT 2
STYLE 26: PIN 1. 2. 3.	V <sub>CC</sub> GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE SOURCE
STYLE 31: PIN 1. 2. 3.	GATE DRAIN SOURCE	STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN INPUT OUTPUT	STYLE 34: PIN 1. 2. 3.	INPUT Ground Logic	STYLE 35: PIN 1. 2. 3.	GATE COLLECTOR EMITTER

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 2 OF 2		
ON Semiconductor and Mara trademarks of Semiconductor Components Industries LLC day ON Semiconductor or its subsidiaries in the United States and/or other countries					

ON Semiconductor and u are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights or the rights of others.





\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	SCRIPTION: SOIC-8 NB						
ON Semiconductor reserves the right the suitability of its products for any pa	ON Semiconductor and a re trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.						

© Semiconductor Components Industries, LLC, 2019

#### SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2
ON Semiconductor and ()) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or criccuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the			

SOURCE 1/DRAIN 2

7.

8. GATE 1

COLLECTOR, #2

COLLECTOR, #1

COLLECTOR, #1

6.

7.

8

rights of others

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor date sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use a a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor houteds for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

#### TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910 Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative